

## **isc Silicon NPN Power Transistor**

# 2SD2539

### DESCRIPTION

- High Breakdown Voltage-
  - : V<sub>CBO</sub>= 1500V (Min)
- High Switching Speed
- Low Saturation Voltage
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

SYMBOL

Vсво

VCEO

 $V_{\text{EBO}}$ 

lc

I<sub>CP</sub>

 $I_B$ 

 $\mathsf{P}_\mathsf{C}$ 

ТJ

Tstg

· Designed for color TV horizontal output applications

VALUE

1500

600

5

7

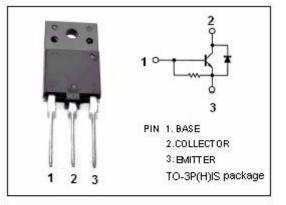
14

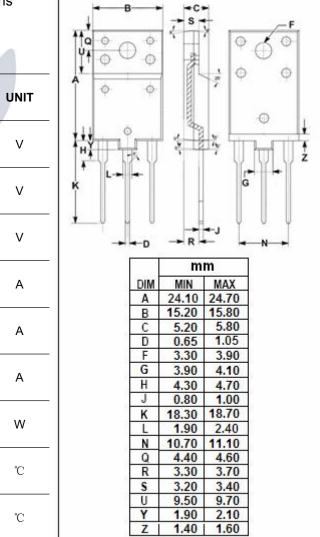
3.5

50

150

-55~150





#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

Collector-Base Voltage

Collector-Emitter Voltage

Collector Current- Continuous

Collector Current- Pulse

**Base Current- Continuous** 

**Collector Power Dissipation** 

Storage Temperature Range

Junction Temperature

@ Tc=25°C

Emitter-Base Voltage

PARAMETER

isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 200mA ; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			5.0	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.3	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0	66		200	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 5V	8		28	
h <sub>FE-2</sub>	DC Current Gain	Ic= 5A ; V <sub>CE</sub> = 5V	5		9	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 5A			2.0	V
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		2		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		115		pF
t <sub>stg</sub>	Storage Time	I <sub>CP</sub> = 5A , I <sub>B1(end)</sub> = 1.0A; f <sub>H</sub> = 15.75kHz		6	9	μ <b>S</b>
tf	Fall Time			0.3	0.6	μs

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